## INTEGRATED CIRCUITS

## DATA SHEET

# **74LVC10A**Triple 3-input NAND gate

**Product specification** 

1998 Apr 28





## **Triple 3-input NAND gate**

**74LVC10A** 

#### **FEATURES**

- Wide supply voltage range of 1.2 V to 3.6 V
- In accordance with JEDEC standard no. 8-1A.
- Inputs accept voltages up to 5.5 V
- CMOS low power consumption
- Direct interface with TTL levels
- Output capability: standard
- I<sub>CC</sub> category: SSI

#### **DESCRIPTION**

The 74LVC10A is a high performance, low power, low voltage, Si gate CMOS device and superior to most advanced CMOS compatible TTL families.

The 74LVC10A provides the 3-input NAND function.

#### **QUICK REFERENCE DATA**

GND = 0 V;  $T_{amb} = 25^{\circ}C$ ;  $t_r = t_f \le 2.5 \text{ ns}$ 

SYMBOL	PARAMETER	CONDITIONS	TYPICAL	UNIT
t <sub>PHL</sub> /t <sub>PLH</sub>	Propagation delay nA, nB, nC to nY	$C_L = 50 \text{ pF};$ $V_{CC} = 3.3 \text{ V}$	3.9	ns
C <sub>I</sub>	Input capacitance		5.0	pF
C <sub>PD</sub>	Power dissipation capacitance per gate	$V_I = GND \text{ to } V_{CC}^{-1}$	26	pF

#### NOTE:

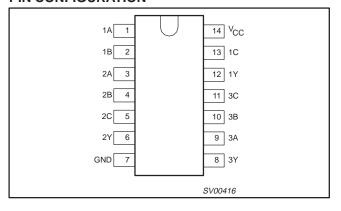
1.  $C_{PD}$  is used to determine the dynamic power dissipation ( $P_D$  in  $\mu W$ )

P<sub>D</sub> = C<sub>PD</sub> × V<sub>CC</sub><sup>2</sup> × f<sub>i</sub> +  $\sum$  (C<sub>L</sub> × V<sub>CC</sub><sup>2</sup> × f<sub>o</sub>) where: f<sub>i</sub> = input frequency in MHz; C<sub>L</sub> = output load capacity in pF; f<sub>o</sub> = output frequency in MHz; V<sub>CC</sub> = supply voltage in V;  $\sum$  (C<sub>L</sub> × V<sub>CC</sub><sup>2</sup> × f<sub>o</sub>) = sum of the outputs.

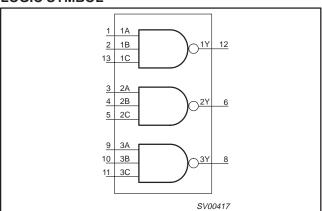
#### ORDERING INFORMATION

PACKAGES	TEMPERATURE RANGE	OUTSIDE NORTH AMERICA	NORTH AMERICA	DWG NUMBER
14-Pin Plastic SO	-40°C to +85°C	74LVC10A D	74LVC10A D	SOT108-1
14-Pin Plastic SSOP Type II	-40°C to +85°C	74LVC10A DB	74LVC10A DB	SOT337-1
14-Pin Plastic TSSOP Type I	-40°C to +85°C	74LVC10A PW	74LVC10APW DH	SOT402-1

#### **PIN CONFIGURATION**



#### LOGIC SYMBOL



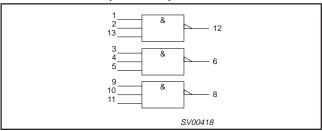
#### PIN DESCRIPTION

PIN NUMBER	SYMBOL	NAME AND FUNCTION
1, 3, 9	1A – 3A	Data inputs
2, 4, 10	1B – 3B	Data inputs
7	GND	Ground (0 V)
12, 6, 8	1Y – 3Y	Data outputs
13, 5, 11	1C – 3C	Data inputs
14	V <sub>CC</sub>	Positive supply voltage

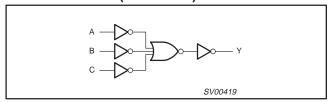
## Triple 3-input NAND gate

74LVC10A

#### LOGIC SYMBOL (IEEE/IEC)



#### **LOGIC DIAGRAM (ONE GATE)**



#### **FUNCTION TABLE**

	INPUTS		OUTPUTS
nA	nB	nC	nY
L	L	L	Н
L	L	Н	Н
L	Н	L	Н
L	Н	Н	Н
Н	L	L	Н
Н	L	Н	Н
Н	Н	L	Н
Н	Н	Н	L

#### NOTES:

H = HIGH voltage level L = LOW voltage level

#### RECOMMENDED OPERATING CONDITIONS

SYMBOL	PARAMETER	CONDITIONS	LIM	UNIT	
STWIBUL	PARAMETER	CONDITIONS	MIN	MAX	UNII
V <sub>CC</sub>	DC supply voltage (for max. speed performance)		2.7	3.6	V
V <sub>CC</sub>	DC supply voltage (for low-voltage applications)		1.2	3.6	V
V <sub>I</sub>	DC input voltage range		0	5.5	V
T <sub>amb</sub>	Operating free-air temperature range		-40	+85	°C
t <sub>r</sub> , t <sub>f</sub>	Input rise and fall times	$V_{CC} = 1.2 \text{ to } 2.7V$ $V_{CC} = 2.7 \text{ to } 3.6V$	0 0	20 10	ns/V

#### **ABSOLUTE MAXIMUM RATINGS<sup>1</sup>**

In accordance with the Absolute Maximum Rating System (IEC 134). Voltages are referenced to GND (ground = 0V).

SYMBOL	PARAMETER	CONDITIONS	RATING	UNIT
V <sub>CC</sub>	DC supply voltage		-0.5 to +6.5	V
I <sub>IK</sub>	DC input diode current	$V_I < 0$	<b>-</b> 50	mA
VI	DC input voltage	Note 2	-0.5 to +6.5	V
I <sub>OK</sub>	DC output diode current	$V_O > V_{CC}$ or $V_O < 0$	±50	mA
\/	DC output voltage; output HIGH or LOW	Note 2	-0.5 to V <sub>CC</sub> +0.5	V
V <sub>I/O</sub>	DC input voltage; output 3-State	Note 2	-0.5 to 6.5	V
I <sub>O</sub>	DC output source or sink current	$V_O = 0$ to $V_{CC}$	±50	mA
I <sub>GND</sub> , I <sub>CC</sub>	DC V <sub>CC</sub> or GND current		±100	mA
T <sub>stg</sub>	Storage temperature range		–65 to +150	°C
P <sub>TOT</sub>	Power dissipation per package  – plastic mini-pack (SO)  – plastic shrink mini-pack (SSOP and TSSOP)	above +70°C derate linearly with 8 mW/K above +60°C derate linearly with 5.5 mW/K	500 500	mW

#### NOTES:

- 1. Stresses beyond those listed may cause permanent damage to the device. These are stress ratings only and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.
- 2. The input and output voltage ratings may be exceeded if the input and output current ratings are observed.

## Triple 3-input NAND gate

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#### DC ELECTRICAL CHARACTERISTICS

Over recommended operating conditions. Voltages are referenced to GND (ground = 0V).

			L			
SYMBOL	PARAMETER	TEST CONDITIONS	Temp = -	UNIT		
			MIN	TYP <sup>1</sup>	MAX	1
V	HIGH level Input voltage	V <sub>CC</sub> = 1.2V	V <sub>CC</sub>			V
V <sub>IH</sub>	nion level input voltage	V <sub>CC</sub> = 2.7 to 3.6V	2.0			]
V	LOW/ lovel Input voltage	V <sub>CC</sub> = 1.2V			GND	V
V <sub>IL</sub>	LOW level Input voltage	V <sub>CC</sub> = 2.7 to 3.6V			0.8	]
		$V_{CC} = 2.7V$ ; $V_I = V_{IH}$ or $V_{IL}$ ; $I_O = -12mA$	V <sub>CC</sub> - 0.5			
\ \ \	HIGH level output voltage	$V_{CC} = 3.0V$ ; $V_I = V_{IH}$ or $V_{IL}$ ; $I_O = -100\mu A$	V <sub>CC</sub> - 0.2	V <sub>CC</sub>		] ,
V <sub>OH</sub>	HIGH level output voltage	$V_{CC} = 3.0V$ ; $V_I = V_{IH}$ or $V_{IL}$ ; $I_O = -12mA$	V <sub>CC</sub> - 0.6			]
		$V_{CC} = 3.0V$ ; $V_I = V_{IH}$ or $V_{IL}$ ; $I_O = -24$ mA	V <sub>CC</sub> – 1.0			
		$V_{CC} = 2.7V$ ; $V_I = V_{IH}$ or $V_{IL}$ ; $I_O = 12mA$			0.40	
V <sub>OL</sub>	LOW level output voltage	$V_{CC} = 3.0V; V_I = V_{IH} \text{ or } V_{IL}; I_O = 100 \mu A$			0.20	v
		$V_{CC} = 3.0V$ ; $V_I = V_{IH}$ or $V_{IL}$ ; $I_O = 24mA$			0.55	
I <sub>I</sub>	Input leakage current	$V_{CC} = 3.6V; V_I = 5.5V \text{ or GND}$		±0.1	±5	μА
I <sub>CC</sub>	Quiescent supply current	$V_{CC} = 3.6V; V_I = V_{CC} \text{ or GND}; I_O = 0$		0.1	10	μА
Δl <sub>CC</sub>	Additional quiescent supply current per input pin	$V_{CC} = 2.7 \text{V to } 3.6 \text{V}; V_{I} = V_{CC} - 0.6 \text{V}; I_{O} = 0$		5	500	μА

#### NOTE:

#### **AC CHARACTERISTICS**

GND = 0 V;  $t_r$  =  $t_f \leq$  2.5 ns;  $C_L$  = 50 pF

SYMBOL	PARAMETER	WAVEFORM	V <sub>C</sub>	c = 3.3V ±0	.3V	V <sub>CC</sub> =	UNIT	
			MIN	TYP <sup>1</sup>	MAX	MIN	MAX	
t <sub>PHL</sub> / t <sub>PLH</sub>	Propagation delay nA, nB, nC to nY	Figures 1, 2	1.5	3.9	5.7	1.5	6.7	ns

#### **AC WAVEFORMS**

 $V_M$  = 1.5 V at  $V_{CC} \ge 2.7 \text{ V}$ 

 $V_{M}$  = 0.5 •  $V_{CC}$  at  $V_{CC}$  < 2.7 V  $V_{OL}$  and  $V_{OH}$  are the typical output voltage drop that occur with the output load.

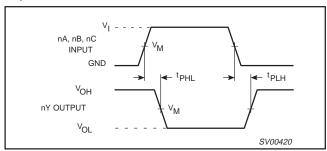


Figure 1. Input (nA, nB, nC) to output (nY) propagation delays.

#### **TEST CIRCUIT**

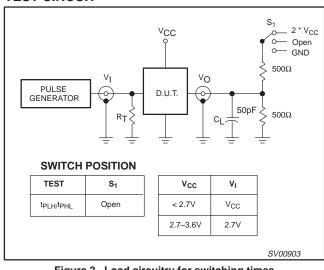


Figure 2. Load circuitry for switching times.

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<sup>1.</sup> All typical values are at  $V_{CC}$  = 3.3V and  $T_{amb}$  = 25°C.

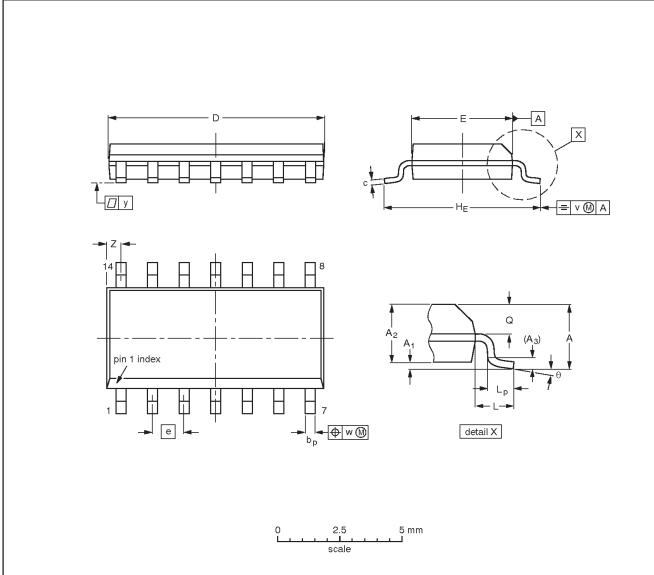
<sup>1.</sup> These typical values are at  $V_{CC}$  = 3.3V and  $T_{amb}$  = 25°C.

## Triple 3-input NAND gate

74LVC10A

#### SO14: plastic small outline package; 14 leads; body width 3.9 mm

SOT108-1



#### DIMENSIONS (inch dimensions are derived from the original mm dimensions)

UNIT	A max.	A <sub>1</sub>	A <sub>2</sub>	А3	bp	С	D <sup>(1)</sup>	E <sup>(1)</sup>	е	HE	L	Lp	Q	v	w	у	Z <sup>(1)</sup>	θ
mm	1.75	0.25 0.10	1.45 1.25	0.25	0.49 0.36	0.25 0.19	8.75 8.55	4.0 3.8	1.27	6.2 5.8	1.05	1.0 0.4	0.7 0.6	0.25	0.25	0.1	0.7 0.3	8°
inches	0.069	0.010 0.004	0.057 0.049	0.01		0.0100 0.0075		0.16 0.15	0.050	0.244 0.228	0.041	0.039 0.016	0.028 0.024	0.01	0.01	0.004	0.028 0.012	o°

#### Note

1. Plastic or metal protrusions of 0.15 mm maximum per side are not included.

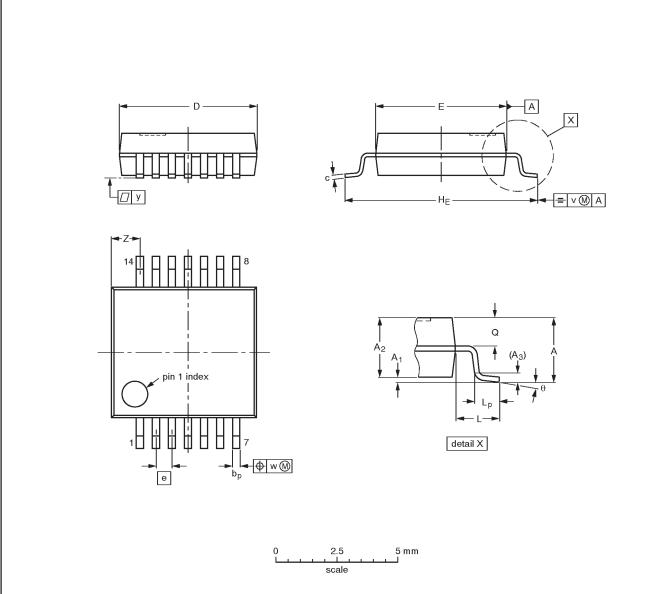
OUTLINE		REFER	RENCES	EUROPEAN	ISSUE DATE
VERSION	IEC	JEDEC	EIAJ	PROJECTION	ISSUE DATE
SOT108-1	076E06S	MS-012AB			<del>-95-01-23-</del> 97-05-22

## Triple 3-input NAND gate

74LVC10A

SSOP14: plastic shrink small outline package; 14 leads; body width 5.3 mm

SOT337-1



#### DIMENSIONS (mm are the original dimensions)

UNIT	A max.	A <sub>1</sub>	A <sub>2</sub>	<b>A</b> <sub>3</sub>	bp	c	D <sup>(1)</sup>	E <sup>(1)</sup>	e	HE	L	Lp	Q	v	w	у	Z <sup>(1)</sup>	θ
mm	2.0	0.21 0.05	1.80 1.65	0.25	0.38 0.25	0.20 0.09	6.4 6.0	5.4 5.2	0.65	7.9 7.6	1.25	1.03 0.63	0.9 0.7	0.2	0.13	0.1	1.4 0.9	8° 0°

#### Note

1. Plastic or metal protrusions of 0.25 mm maximum per side are not included.

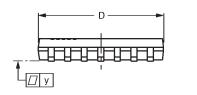
OUTLINE		REFER	RENCES		EUROPEAN	ISSUE DATE	
VERSION	IEC	JEDEC	JEDEC EIAJ		PROJECTION	1990E DATE	
SOT337-1		MO-150AB				<del>95-02-04</del> 96-01-18	

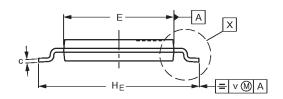
## Triple 3-input NAND gate

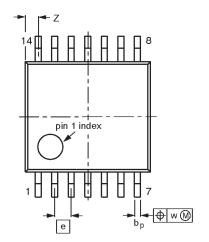
74LVC10A

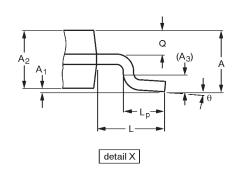
TSSOP14: plastic thin shrink small outline package; 14 leads; body width 4.4 mm

SOT402-1











#### DIMENSIONS (mm are the original dimensions)

UNIT	A max.	Α1	A <sub>2</sub>	A <sub>3</sub>	рb	С	D <sup>(1)</sup>	E <sup>(2)</sup>	е	HE	L	Lp	Q	v	w	у	Z <sup>(1)</sup>	θ
mm	1.10	0.15 0.05	0.95 0.80	0.25	0.30 0.19	0.2 0.1	5.1 4.9	4.5 4.3	0.65	6.6 6.2	1.0	0.75 0.50	0.4 0.3	0.2	0.13	0.1	0.72 0.38	8° 0°

#### Notes

- 1. Plastic or metal protrusions of 0.15 mm maximum per side are not included.
- 2. Plastic interlead protrusions of 0.25 mm maximum per side are not included.

OUTLINE		REFER	EUROPEAN	ISSUE DATE		
VERSION	IEC	JEDEC	EIAJ		PROJECTION	ISSUE DATE
SOT402-1		MO-153				<del>94-07-12</del> 95-04-04

### Triple 3-input NAND gate

74LVC10A

#### Data sheet status

Data sheet status	Product status	Definition [1]
Objective specification	Development	This data sheet contains the design target or goal specifications for product development. Specification may change in any manner without notice.
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